

DP2101W

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P-Channel Enhancement Mode Field Effect Transistor

General description

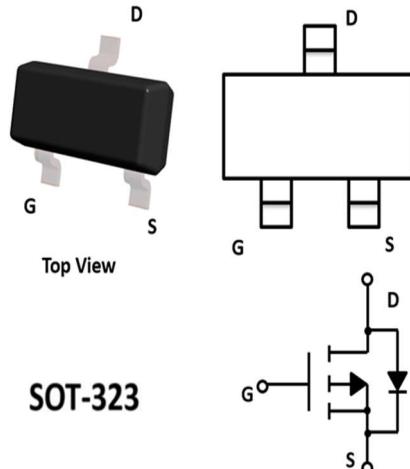
P-Channel Enhancement Mode Field Effect Transistor

Features:

- V_{DS} : -20V
- I_D : -2.0A
- $R_{DS(ON)}$ (at $V_{GS}=-4.5V$) < 120 mohm
- $R_{DS(ON)}$ (at $V_{GS}=-2.5V$) < 150 mohm
- Trench Power LV MOSFET technology
- Low $R_{DS(ON)}$
- Low Gate Charge

Applications

- Video monitor
- Power management



Device Marking Code:

Device Type	Device Marking
DP2101W	TS1

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Maximum	Unit
Drain-source Voltage	V_{DS}	-20	V
Gate-source Voltage	V_{GS}	± 10	V
Drain Current	I_D	-2	A
		-1.6	
Pulsed Drain Current ^A	I_{DM}	-8	A
Total Power Dissipation @ $T_A=25^\circ C$	P_D	0.7	W
Thermal Resistance Junction-to-Ambient ^B	$R_{\theta JA}$	178	$^\circ C / W$
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^\circ C$

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Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-20			V
Zero Gate Voltage Drain Current	$I_{\text{DS}}^{\text{SS}}$	$V_{\text{DS}}=-20\text{V}, V_{\text{GS}}=0\text{V}, T_c=25^\circ\text{C}$			-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}}= \pm 10\text{V}, V_{\text{DS}}=0\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-0.4	-0.62	-1.0	V
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}= -4.5\text{V}, I_{\text{D}}=-1.5\text{A}$		90	120	$\text{m}\Omega$
		$V_{\text{GS}}= -2.5\text{V}, I_{\text{D}}=-1.5\text{A}$		115	150	
Diode Forward Voltage	V_{SD}	$I_{\text{S}}=-2\text{A}, V_{\text{GS}}=0\text{V}$		-0.8	-1.2	V
Maximum Body-Diode Continuous Current	I_{S}				-2	A
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{\text{DS}}=-10\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$		290		pF
Output Capacitance	C_{oss}			47		
Reverse Transfer Capacitance	C_{rss}			29		
Switching Parameters						
Total Gate Charge	Q_{g}	$V_{\text{GS}}=-4.5\text{V}, V_{\text{DS}}=-10\text{V}, I_{\text{D}}=-2\text{A}$		3.9		nC
Gate Source Charge	Q_{gs}			0.7		
Gate Drain Charge	Q_{gd}			0.9		
Turn-on Delay Time	$t_{\text{D(on)}}$	$V_{\text{GS}}=-4.5\text{V}, V_{\text{DD}}=-10\text{V}, I_{\text{D}}=-1\text{A}, R_{\text{GEN}}=2.5\Omega$		12		ns
Turn-on Rise Time	t_{r}			54		
Turn-off Delay Time	$t_{\text{D(off)}}$			15		
Turn-off Fall Time	t_{f}			9		

A.Pulse Test: Pulse Width $\leqslant 300\text{us}$, Duty cycle $\leqslant 2\%$.

B.Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

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Typical Performance Characteristics

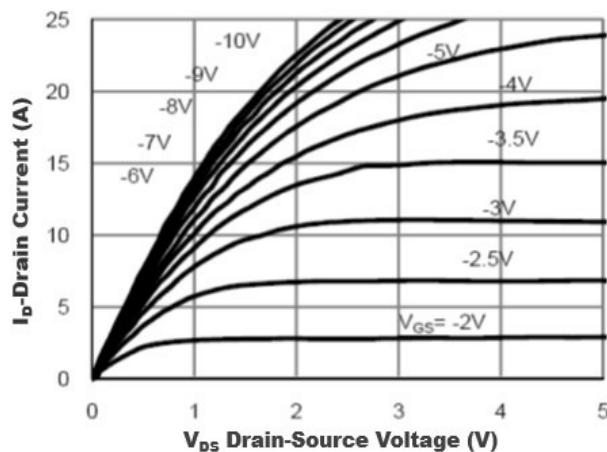


Figure1. Output Characteristics

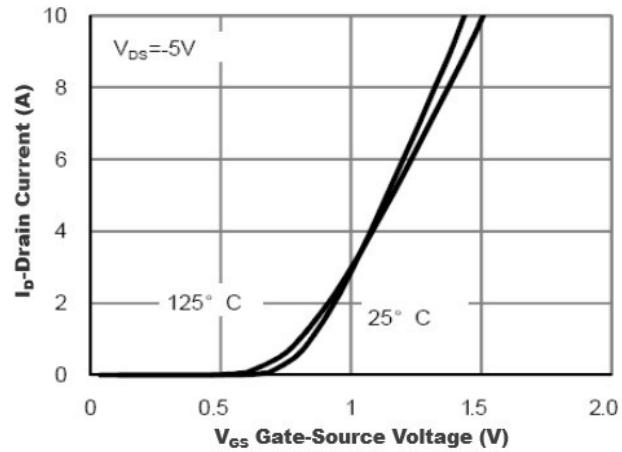


Figure2. Transfer Characteristics

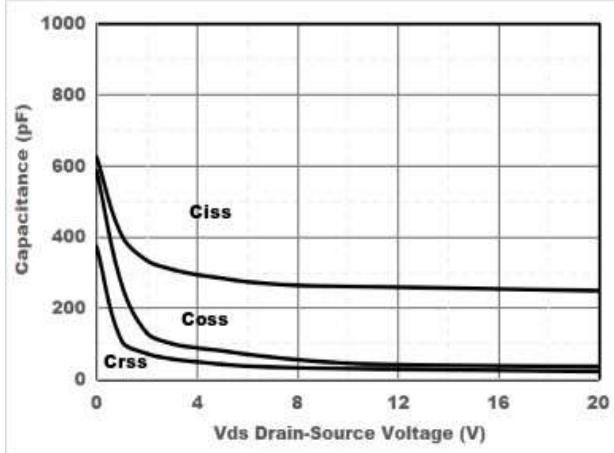


Figure3. Capacitance Characteristics

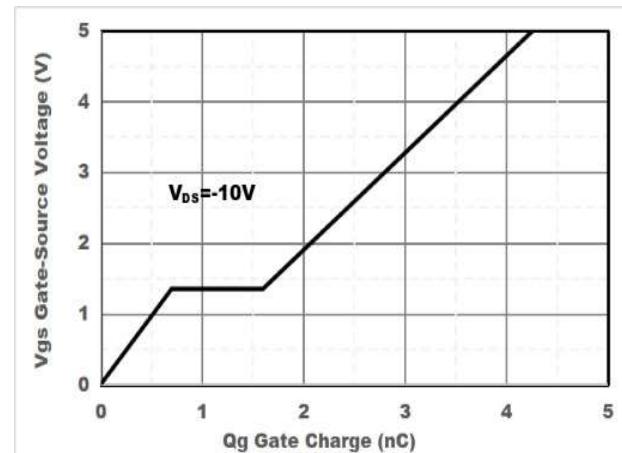


Figure4. Gate Charge

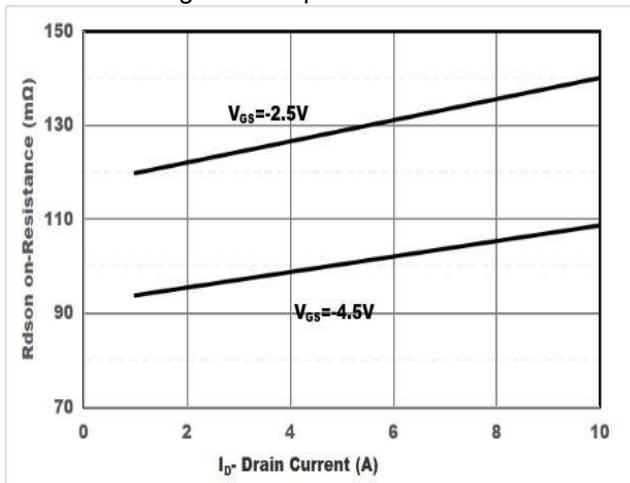


Figure5. Drain-Source on Resistance

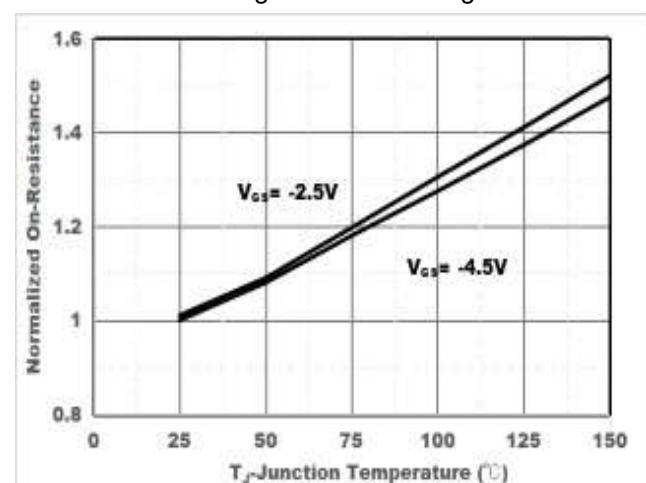
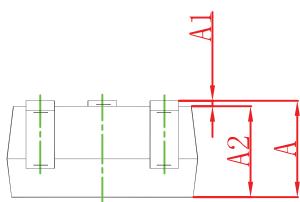
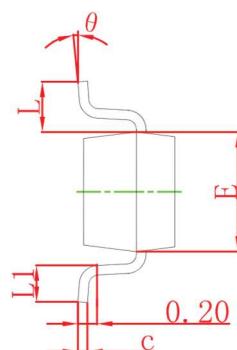
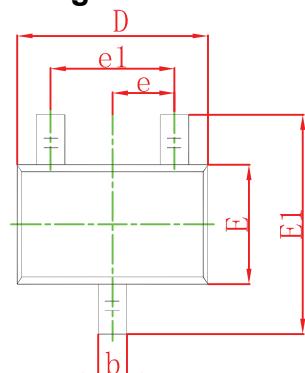
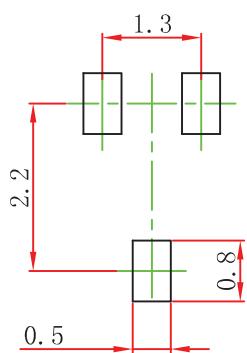


Figure6. Drain-Source on Resistance

SOT-323 Package Outline



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
	0°	8°	0°	8°



Note:

1. Controlling dimension:in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

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